













ESD

TVS

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GDT

PLED



Product specification



SEMICONDUCTOR

TRANSISTOR (NPN)

FEATURES

• power switching applications

Reference News

PACKAGE OUTLINE		MARKING	
	1. BASE 2. EMITTER 3.COLLECTOR	:01CT	
SOT-23			

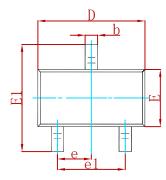
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

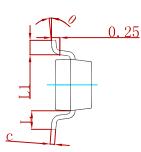
Symbol	Parameter	Value	Unit
Vсво	Collector -Base Voltage	700	V
VCEO	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
lc	Collector Current -Continuous	0.2	A
Pc	Collector Power Dissipation	0.35	W
TJ	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C

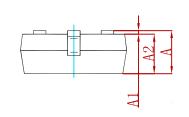
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	l _c = 1mA ,I _E =0	700			V
Collector-emitter breakdown voltage	V(BR)CEO	lc= 1mA ,lв=0	400			V
Emitter-base breakdown voltage	V(BR)EBO	l _E = 100μΑ, I _C =0	9			V
Collector cut-off current	Ісво	V_{CB} = 600V , I _E =0			10	μA
Emitter cut-off current	Іево	V _{EB} =9V, I _C =0			10	μA
DC current gain	hfe(1)	V _{CE} = 10V, I _C = 20mA	10		40	
Collector-emitter saturation voltage	V _{CE(sat)}	l _c = 100mA, I _B = 20 mA			0.5	V
Base-emitter saturation voltage	VBE(sat)	I _C = 100mA, I _B = 20mA			1.2	V
Transition frequency	f⊤	V _{CE} = 20V, I _C =20mA f = 1MHz	5			MHz
Storage time	ts	lc=100mA			3.5	μs

PACKAGE MECHANICAL DATA

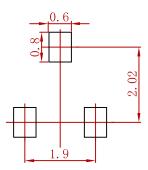






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters. 2.General tolerance:± 0.05mm. 3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MS13001	SOT-23	3000



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